PATENT

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**REVOCATION OF POWER OF ATTORNEY,
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CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

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Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patents or patent applications identified to Renesas Technology Corp. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong Taek Kong

Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: July 7, 2008

APPENDIX A

Application No.	Patent No.	Filing Date	Title of Patent
08/841612	5,870,218	04/30/1997	Non-volatile Semiconductor Memory Device Which Stores Multi-Value Information
09/096457	5,982.667	06/11/1998	Non-volatile Semiconductor Memory Device For Storing Multivalue Information By Controlling Erase And Plural Write States of Each Memory Cell
09/339960	6,181,603	06/25/1999	Non-volatile Semiconductor Memory Device Having Plural Memory Cells Which Store Multi-Value Information
09/715106	6,396,736	11/20/2000	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
10/154853	6,771,537	05/28/2002	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
10/832311	7,031,187	April 27, 2004	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/332206	7,245,532	January 17, 2006	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/595880		November 13, 2006	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information

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12/117918		May 9, 2008	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
07/704739	5,300,802	May 20, 1991	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/179960	5,407,853	January 11, 1994	Method of Making Semiconductor Integrated Circuit Device Having Single-Element Type Non-Volatile Memory Elements
08/422941	5,656,839	April 17, 1995	Semiconductor Integrated Circuit Device Having Single-Element Type Nonvolatile Memory Elements
08/422940	5,629,541	April 17, 1995	Semiconductor Memory Device Constituted by Single Transistor Type Non-volatile Cells and Facilitated for Both Electrical Erasing and Writing of Data
08/451268	5,656,522	May 30, 1995	Method of Manufacturing a Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/885184	5,904,518	June 30, 1997	Method of Manufacturing a Semiconductor IC Device Having Single Transistor Type Nonvolatile Memory Cells
09/282204	6,255,690	March 31, 1999	Non-volatile Semiconductor Memory Device
09/873451	6,451,643	June 5, 2001	Method of Manufacturing a Semiconductor Device Having Non-volatile Memory Cell Portion with

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			Single Transistor Type Memory Cells and Peripheral Portion with MISFETs
10/164626	6,777,282	June 10, 2002	Method of Manufacturing a Semiconductor Memory Device Having a Memory Cell Portion Including MISFETs With a Floating Gate and a Peripheral Circuit Portion With MISFETs
10/819205	6,960501	April 7, 2004	Method of Manufacturing a Semiconductor Memory Device Having a Non-volatile Memory Cell Portion with Single MISFET Transistor Type Memory Cells and a Peripheral Circuit Portion with MISFETs
11/220723	7,071,050	September 8, 2005	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
11/393774		March 31, 2006	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/913338	5,978,941	September 11, 1997	Semiconductor Memory Device Having Deterioration Determining Function
09/432389	6,223,311	November 2, 1999	Semiconductor Memory Device Having Deterioration Determining Function
09/794073	6,694,460	February 28, 2001	Semiconductor Memory Device Having Deterioration Determining Function

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07/517386	5,079,603	April 30, 1990	Semiconductor Memory Device
07/765065	5,189,497	September 24, 1991	Semiconductor Memory Device
07/992473	5,340,760	December 15, 1992	Method of Manufacturing EEPROM Memory Device
08/260229	5,472,891	June 14, 1994	Method of Manufacturing a Semiconductor Device
08/419232	5,604,142	April 10, 1995	Method of Making an EPROM With Peripheral Transistor
11/082992	7,242,611	March 18, 2005	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
11/819015		June 25, 2007	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
11/819016		June 25, 2007	Non-volatile Semiconductor Memory Device for Writing Multivalued Data
09/620719	6,496,409	July 20, 2000	Variable Capacity Semiconductor Memory Device
08/203303	5,422,856	March 1, 1994	Non-volatile Memory Programming at Arbitrary Timing Based on Curren Requirements
10/700592	7,068,541	November 5, 2003	Nonvolatile Memory and Method of Erasing for Nonvolatile Memory
11/284949	7,072,224	November 23,2005	Nonvolatile Memory and Method of Erasing for Nonvolatile Memory